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**PALM INTRANET**

# Inventor Information for 10/796086

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KISHI, TATSUYA	KANAGAWA-KEN	JAPAN








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US 20060132990 A1	20060622	Magnetic recording element, magnetic recording apparatus and recording method of information	360/324.12		Morise; Hirofumi et al.
US 20060132984 A1	20060622	Magnetic memory device having yoke layer on write interconnection and method of manufacturing the same	360/317		Kajiyama; Takeshi et al.
US 20060126230 A1	20060615	Magnetoresistance effect element, magnetic head and magnetic reproducing system	360/322		Yuasa; Hiromi et al.
US 20060126228 A1	20060615	Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus	360/315		Yoshikawa; Masatoshi et al.
US 20060120126 A1	20060608	Magnetic cell and magnetic memory	365/33		Nakamura; Shiho et al.
US 20060114716 A1	20060601	Magnetoresistance element, magnetic memory, and magnetic head	365/158	365/171	Kai; Tadashi et al.
US 20060083057 A1	20060420	Magnetoresistive element	365/171		Nakayama; Masahiko et al.
US 20060082933 A1	20060420	Magnetoresistive element	360/324.11	360/324.12	Kishi; Tatsuya et al.
US 20060071287 A1	20060406	Magnetoresistance effect element, magnetic head and magnetic reproducing apparatus	257/421		Yuasa; Hiromi et al.
US 20060060989 A1	20060323	Magnetic recording element and device		257/903	Morise; Hirofumi et al.
US 20060060901 A1	20060323	Magnetic recording element and magnetic recording device	257/295		Nakamura; Shiho et al.

		using the same			
US 20060007730 A1	20060112	Magnetic cell and magnetic memory	365/171		Nakamura; Shiho et al.
US 20060002185 A1	20060105	Magnetic cell and magnetic memory	365/171		Nakamura; Shiho et al.
US 20050281079 A1	20051222	Magnetic random access memory and method of manufacturing the same	365/158		Yoda, Hiroaki et al.
US 20050280043 A1	20051222	Magnetoresistive element and magnetic memory	257/222		Kai, Tadashi et al.
US 20050275000 A1	20051215	MRAM and method of manufacturing the same	257/295		Kajiyama, Takeshi et al.
US 20050274984 A1	20051215	Semiconductor integrated circuit device and method of manufacturing the same	257/211	257/E27.005	Hosotani, Keiji et al.
US 20050259464 A1	20051124	Magnetic random access memory	365/171		Kajiyama, Takeshi et al.
US 20050219768 A1	20051006	Magneto-resistance effect element	360/324.1		Nakamura, Shiho et al.
US 20050219767 A1	20051006	Magneto-resistive element	360/324.1	360/324.2	Nakamura, Shiho et al.
US 20050199925 A1	20050915	Magnetic random access memory	257/295		Kajiyama, Takeshi et al.
US 20050190594 A1	20050901	Magnetic element and magnetic element array	365/171		Nakamura, Shiho et al.
US 20050185347 A1	20050825	Magnetoresistive element and magnetic memory device	360/324.2	257/E21.665; 257/E27.005	Inomata, Koichiro et al.
US 20050170218 A1	20050804	Magnetoresistive effect element, magnetic memory and magnetic head	428/828		Kishi, Tatsuya et al.
US	20050804	Magnetoresistance	257/421		Fukuzawa,

20050167770 A1		effect element, magnetic head, magnetic head assembly, magnetic storage system			Hideaki et al.
US 20050152077 A1	20050714	Magnetoresistive device, magnetoresistive head and magnetic recording- reproducing apparatus	360/324.11	360/324.12; 365/158; 365/173	Yuasa, Hiromi et al.
US 20050152074 A1	20050714	Magnetoresistance effect element, magnetic head and magnetic reproducing system	360/322	257/E43.004	Yuasa, Hiromi et al.
US 20050141148 A1	20050630	Magnetic memory	360/324.11		Aikawa, Hisanori et al.
US 20050117391 A1	20050602	Magnetic random access memory	365/171		Yoda, Hiroaki et al.
US 20050105325 A1	20050519	Magnetic cell and magnetic memory	365/154		Haneda, Shigeru et al.
US 20050099724 A1	20050512	Magnetic device and magnetic memory	360/125		Nakamura, Shiho et al.
US 20050094327 A1	20050505	Magnetoresistance effect element, its manufacturing method, magnetic reproducing element and magnetic memory	360/324.2		Okuno, Shiho et al.
US 20050083745 A1	20050421	Magnetic memory	365/202		Kishi, Tatsuya et al.
US 20050083613 A1	20050421	Magnetoresistive head and perpendicular magnetic recording- reproducing apparatus	360/324.1		Yoshikawa, Masatoshi et al.
US 20050078418 A1	20050414	Ferromagnetic double tunnel junction element with asymmetric energy	360/324.2	360/314	Saito, Yoshiaki et al.

		band			
US 20050078417 A1	20050414	Magnetoresistance effect device, method of manufacturing the same, magnetic memory apparatus, personal digital assistance, and magnetic reproducing head, and magnetic information reproducing apparatus	360/324.2	257/E21.665; 257/E27.005; 29/603.18; 365/158	Kishi, Tatsuya et al.
US 20050069732 A1	20050331	Magnetic recording medium and method for manufacturing the same	428/835	428/328; 428/336	Kamata, Yoshiyuki et al.
US 20050052795 A1	20050310	Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus	360/324.12		Yoshikawa, Masatoshi et al.
US 20050052794 A1	20050310	Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus	360/324.12		Yoshikawa, Masatoshi et al.
US 20050047202 A1	20050303	Magnetic random access memory having test circuit and test method therefor	365/158		Shimizu, Yuui et al.
US 20050047026 A1	20050303	Magnetoresistance effect element, magnetic head and magnetic reproducing system	360/322	257/E43.004	Yuasa, Hiromi et al.
US 20050042478 A1	20050224	Magnetoresistance effect element, its manufacturing method, magnetic reproducing element and magnetic memory	428/828		Okuno, Shiho et al.
US 20050030676 A1	20050210	Magnetoresistance effect element, magnetic head, magnetic head assembly, magnetic	360/325	428/336; 428/591; 428/611; 428/686	Fukuzawa, Hideaki et al.

		storage system			
US 20050024930 A1	20050203	MAGNETIC MEMORY DEVICE HAVING YOKE LAYER, AND MANUFACTURING METHOD THEREOF	365/158		Yoda, Hiroaki et al.
US 20050018478 A1	20050127	Magnetic random access memory device having thermal agitation property and high write efficiency	365/171		Nagase, Toshihiko et al.
US 20040257866 A1	20041223	Magnetic memory	365/171		Amano, Minoru et al.
US 20040246634 A1	20041209	Magnetoresistance effect element, magnetic head and magnetic reproducing apparatus	360/324.11	360/324.12	Yuasa, Hiromi et al.
US 20040223382 A1	20041111	Magnetic memory	365/200		Saito, Yoshiaki et al.
US 20040195602 A1	20041007	Magnetic random access memory device having high- heat disturbance resistance and high write efficiency	257/295	257/E21.665; 257/E27.005	Yoda, Hiroaki et al.
US 20040179393 A1	20040916	Magnetic random access memory and method of manufacturing the same	365/158		Yoda, Hiroaki et al.
US 20040175596 A1	20040909	Magnetoresistive element and magnetic memory device	428/811.2	257/E21.665; 257/E27.005; 360/324.2; 365/171; 428/812	Inomata, Koichiro et al.
US 20040169963 A1	20040902	Magnetoresistance effect element, its manufacturing method, magnetic reproducing element and magnetic memory	428/693.1		Okuno, Shiho et al.

US 20040169006 A1	20040902	Magnetoresistance effect element and method for producing same	216/27	257/E43.006	Hashimoto, Susumu et al.
US 20040165425 A1	20040826	Magnetic cell and magnetic memory	365/171		Nakamura, Shiho et al.
US 20040156232 A1	20040812	Magnetic memory	365/171		Saito, Yoshiaki et al.
US 20040156231 A1	20040812	Magnetic memory	365/158	257/E21.665; 257/E27.005	Saito, Yoshiaki et al.
US 20040152227 A1	20040805	MAGNETIC MEMORY DEVICE HAVING YOKE LAYER, AND MANUFACTURING METHOD	438/48		Yoda, Hiroaki et al.
US 20040141367 A1	20040722	Magneto-resistance effect element and magnetic memory	365/158		Amano, Minoru et al.
US 20040121185 A1	20040624	Magnetoresistance effect element, magnetic head, magnetic head assembly, magnetic storage system	428/815	324/252; 338/32R; 360/122; 428/816	Fukuzawa, Hideaki et al.
US 20040100818 A1	20040527	Magnetic random access memory	365/173		Yoda, Hiroaki et al.
US 20040085681 A1	20040506	Magnetoresistance element, magnetic memory, and magnetic head	360/313		Kai, Tadashi et al.
US 20040076035 A1	20040422	Magnetic memory	365/158		Saito, Yoshiaki et al.
US 20040062938 A1	20040401	Magnetoresistive element and magnetic memory	428/469	428/209	Kai, Tadashi et al.
US 20040061980 A1	20040401	Magneto-resistance effect element	360/324	438/3	Haneda, Shigeru et al.
US 20040061590	20040401	Magneto-resistance effect element and	338/32R		Kamiguchi, Yuzo et al.

A1		reproducing head			
US 20040021189 A1	20040205	MAGNETIC MEMORY DEVICE HAVING YOKE LAYER, AND MANUFACTURING METHOD THEREOF	257/421		Yoda, Hiroaki et al.
US 20040004889 A1	20040108	Magnetic random access memory	365/222		Asao, Yoshiaki et al.
US 20030227807 A1	20031211	Magnetic logic element and magnetic logic element array	365/202		Nakamura, Shiho et al.
US 20030214862 A1	20031120	Magnetic random access memory	365/200		Asao, Yoshiaki et al.
US 20030197984 A1	20031023	Magnetoresistive element and magnetic memory device	360/324.2	257/E21.665; 257/E27.005; 360/314; 365/158	Inomata, Koichiro et al.
US 20030186552 A1	20031002	Method for producing magnetic memory device	438/694		Amano, Minoru et al.
US 20030185050 A1	20031002	Magnetoresistance element and magnetic memory	365/173		Kishi, Tatsuya et al.
US 20030168673 A1	20030911	Magnetoresistance effect element, magnetic head and magnetic reproducing apparatus	257/200	257/E43.005	Yuasa, Hiromi et al.
US 20030161181 A1	20030828	Magnetic memory	365/173	360/324; 360/324.12; 360/324.2; 365/158	Saito, Yoshiaki et al.
US 20030156476 A1	20030821	Magnetic memory	365/200		Kishi, Tatsuya et al.
US 20030137870 A1	20030724	Magnetic memory	365/158	257/E21.665; 257/E27.005	Saito, Yoshiaki et al.
US 20030137028 A1	20030724	Semiconductor integrated circuit device and method of manufacturing the	257/528	257/536; 257/E27.005; 438/3; 438/381	Hosotani, Keiji et al.

		same			
US 20030123283 A1	20030703	Magnetic memory	365/173	365/171	Amano, Minoru et al.
US 20030104249 A1	20030605	Magnetoresistance effect element, its manufacturing method, magnetic reproducing element and magnetic memory	428/811.1	428/811.5	Okuno, Shiho et al.
US 20030062975 A1	20030403	Magnetoresistive effect element, magnetic memory and magnetic head	335/106		Kishi, Tatsuya et al.
US 20030011940 A1	20030116	Magnetic head and magnetic reproducing apparatus	360/321		Tateyama, Kohichi et al.
US 20020191451 A1	20021219	Magnetoresistance effect device	365/200	257/E43.004	Kishi, Tatsuya et al.
US 20020159203 A1	20021031	Magnetoresistance effect element	360/324.2	365/158	Saito, Yoshiaki et al.
US 20020150791 A1	20021017	Magnetoresistive device, magnetoresistive head and magnetic recording- reproducing apparatus	428/811		Yuasa, Hiromi et al.
US 20020141232 A1	20021003	Magnetic memory device	365/158		Saito, Yoshiaki et al.
US 20020135954 A1	20020926	Magnetoresistive head and perpendicular magnetic recording- reproducing apparatus	360/324.12		Yoshikawa, Masatoshi et al.
US 20020135948 A1	20020926	Magnetoresistive effect element, its Manufacturing method, magnetic head, magnetic reproducing apparatus, and magnetic memory	360/324.1	257/E21.665; 257/E27.005; 29/603.14; 360/322; 365/158	Funayama, Tomomi et al.
US	20020919	Magnetoresistance	257/295	257/E21.665;	Kishi,

20020130339 A1		effect device, method of manufacturing the same, magnetic memory apparatus, personal digital assistance, and magnetic reproducing head, and magnetic information reproducing apparatus		257/E27.005	Tatsuya et al.
US 20020101328 A1	20020801	Magnetoresistance effect element and method for producing same	338/32R	257/E43.006; 333/201	Hashimoto, Susumu et al.
US 20020048690 A1	20020425	Magnetoresistance effect element, magnetic head, magnetic head assembly, magnetic storage system	428/811		Fukuzawa, Hideaki et al.
US 20020039265 A1	20020404	Magnetoresistance effect element, magnetic head and magnetic reproducing system	360/322	257/E43.004; 360/324.1	Yuasa, Hiromi et al.
US 20020039264 A1	20020404	Yoke type magnetic head and magnetic disk unit	360/322	360/324.1; 360/324.2	Ohsawa, Yuichi et al.
US 20020034094 A1	20020321	Magnetic memory	365/158	257/E21.665; 257/E27.005; 365/171	Saito, Yoshiaki et al.
US 20020015269 A1	20020207	Magnetoresistance effect device, magnetic head therewith, magnetic recording/reproducing head, and magnetic storing apparatus	360/324.12	257/E21.665; 257/E27.005	Iwasaki, Hitoshi et al.
US 20020009616 A1	20020124	Multi-layered thin-film functional device and magnetoresistance effect element	428/811		Kamiguchi, Yuzo et al.
US 20010043448 A1	20011122	Magnetoresistance effect device, magnetic head	360/324.12	257/E21.665; 257/E27.005; 360/324.11	Iwasaki, Hitoshi et al.

		therewith, magnetic recording/reproducing head, and magnetic storing apparatus			
US 20010013999 A1	20010816	Magnetoresistive element and magnetic recording apparatus	360/324.11	360/314	Koi, Katsuhiko et al.
US 7064402 B2	20060620	Magnetic random access memory	257/421	438/48	Kajiyama; Takeshi et al.
US 7061732 B2	20060613	Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus	360/324.12		Yoshikawa; Masatoshi et al.
US 7054187 B2	20060530	Magnetic memory	365/158	365/171	Kishi; Tatsuya et al.
US 7042762 B2	20060509	Magnetic element and magnetic element array	365/173	365/158	Nakamura; Shiho et al.
US 7042758 B2	20060509	Magnetic cell and magnetic memory	365/158	365/171	Haneda; Shigeru et al.
US 7041603 B2	20060509	Method for producing magnetic memory device	438/704	216/22; 216/38; 438/3; 438/692; 438/720; 438/723; 438/724; 438/756; 438/757	Amano; Minoru et al.
US 7038939 B2	20060502	Magneto-resistance effect element and magnetic memory	365/158	365/171; 365/173; 365/230.07	Amano; Minoru et al.
US 7038894 B2	20060502	Magnetoresistive element and magnetic memory device	360/324.2	360/314; 365/158; 365/171; 365/173	Inomata; Koichiro et al.
US 7027273 B2	20060411	Magnetoresistive head with an intermediate layer between first and second magnetization free layers and	360/324.12	360/324.2	Yoshikawa; Masatoshi et al.

		perpendicular magnetic recording-reproducing apparatus			
US 7023725 B2	20060404	Magnetic memory	365/158	365/171	Saito; Yoshiaki et al.
US 7016169 B2	20060321	Magnetoresistive head with first and second pairs of antiferromagnetic films imparting magnetic bias to first and second magnetization free layers and perpendicular magnetic recording-reproducing apparatus	360/324.12		Yoshikawa; Masatoshi et al.
US 7016162 B2	20060321	Magnetoresistance effect element, magnetic head and magnetic reproducing system having pillar electrodes	360/322	257/E43.004	Yuasa; Hiromi et al.
US 7009873 B2	20060307	Magnetic random access memory	365/158	365/182	Yoda; Hiroaki et al.
US 7008702 B2	20060307	Magnetoresistance effect element, magnetic head, magnetic head assembly, magnetic storage system	428/811.2	360/324.12; 428/811.5	Fukuzawa; Hideaki et al.
US 6995962 B2	20060207	Ferromagnetic double tunnel junction element with asymmetric energy band	360/324.2		Saito; Yoshiaki et al.
US 6987653 B2	20060117	Magnetoresistive element and magnetic memory device	360/324.2	257/E21.665; 257/E27.005; 365/171; 365/173	Inomata; Koichiro et al.
US 6984865 B2	20060110	Magnetic random access memory	257/421	438/48	Kajiyama; Takeshi et al.
US 6960815	20051101	Magnetic memory	257/421	257/30	Yoda;

B2		device having yoke layer, and manufacturing method thereof			Hiroaki et al.
US 6958932 B2	20051025	Semiconductor integrated circuit device and method of manufacturing the same	365/171	257/295; 257/E27.005; 365/158	Hosotani; Keiji et al.
US 6956766 B2	20051018	Magnetic cell and magnetic memory	365/171	365/158; 365/173	Nakamura; Shiho et al.
US 6950334 B2	20050927	Magnetic random access memory having test circuit and test method therefor	365/158	365/171; 365/173; 365/200; 365/201	Shimizu; Yuui et al.
US 6949779 B2	20050927	Magnetoresistive element and magnetic memory	257/295	365/158; 365/171; 365/173; 365/66; 365/97; 365/98	Kai; Tadashi et al.
US 6947314 B2	20050920	Magnetic random access memory and method of manufacturing the same	365/158	365/171; 365/173	Yoda; Hiroaki et al.
US 6940700 B2	20050906	Magnetic head and magnetic reproducing apparatus	360/321		Tateyama; Kohichi et al.
US 6937447 B2	20050830	Magnetoresistance effect element, its manufacturing method, magnetic reproducing element and magnetic memory	360/324.1	360/324.2; 428/611; 428/678; 428/686	Okuno; Shiho et al.
US 6934184 B2	20050823	Magnetic memory	365/173	365/157; 365/158	Amano; Minoru et al.
US 6928724 B2	20050816	Magnetoresistance effect element and method for producing same	29/603.07	257/E43.006	Hashimoto; Susumu et al.
US 6927468 B2	20050809	Magnetic random access memory	257/422	257/295; 257/296; 257/421	Yoda; Hiroaki et al.
US 6914807	20050705	Magnetic logic	365/158	365/171;	Nakamura;

B2		element and magnetic logic element array		365/173	Shiho et al.
US 6914757 B2	20050705	Magnetoresistance effect element, magnetic head and magnetic reproducing system	360/322	257/E43.004; 360/324.1; 360/324.2	Yuasa; Hiromi et al.
US 6909130 B2	20050621	Magnetic random access memory device having high-heat disturbance resistance and high write efficiency	257/295	257/678; 257/E21.665; 257/E27.005	Yoda; Hiroaki et al.
US 6906949 B1	20050614	Magnetic element and magnetic element array	365/173	365/158	Nakamura; Shiho et al.
US 6905780 B2	20050614	Current-perpendicular-to-plane-type magnetoresistive device, and magnetic head and magnetic recording-reproducing apparatus using the same	428/611	360/126; 360/324.11; 360/324.12; 428/336; 428/669; 428/676; 428/681; 428/692.1	Yuasa; Hiromi et al.
US 6879515 B2	20050412	Magnetic memory device having yoke layer	365/158	365/171; 365/173	Yoda; Hiroaki et al.
US 6879475 B2	20050412	Magnetoresistive effect element having a ferromagnetic tunneling junction, magnetic memory, and magnetic head	360/324.2	360/324.12	Kishi; Tatsuya et al.
US 6873023 B2	20050329	Magnetic random access memory	257/421	257/30	Asao; Yoshiaki et al.
US 6868002 B2	20050315	Magnetic memory with reduced write current	365/158	257/E21.665; 257/E27.005; 365/117	Saito; Yoshiaki et al.
US 6847509 B2	20050125	Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus	360/324.12		Yoshikawa; Masatoshi et al.
US 6839206	20050104	Ferromagnetic double	360/324.2	360/314	Saito;

B2		tunnel junction element with asymmetric energy band			Yoshiaki et al.
US 6831857 B2	20041214	Magnetic memory	365/173	365/157; 365/158	Amano; Minoru et al.
US 6831855 B2	20041214	Magnetic memory	365/158	365/171	Kishi; Tatsuya et al.
US 6816347 B2	20041109	Magnetoresistive element and magnetic recording apparatus	360/324.11		Koi; Katsuhiko et al.
US 6807094 B2	20041019	Magnetic memory	365/173	365/158; 365/171	Saito; Yoshiaki et al.
US 6797536 B2	20040928	Magnetic memory device having yoke layer, and manufacturing method	438/48	438/3	Yoda; Hiroaki et al.
US 6784509 B2	20040831	Magnetoresistance effect element, magnetic head and magnetic reproducing apparatus	257/421	257/E27.006; 257/E43.005; 360/324.11	Yuasa; Hiromi et al.
US 6770210 B2	20040803	Magnetoresistance effect element and method for producing same	216/22	257/E43.006; 29/603.07	Hashimoto; Susumu et al.
US 6765824 B2	20040720	Magneto-resistance element capable of controlling the position and size of edge domain and the coercivity and magnetic memory	365/173	365/158; 365/171; 365/51	Kishi; Tatsuya et al.
US 6765821 B2	20040720	Magnetic memory	365/158	365/171; 365/175	Saito; Yoshiaki et al.
US 6757143 B2	20040629	Magnetoresistive effect element, its manufacturing method, magnetic head, magnetic reproducing	360/324.1	257/E21.665; 257/E27.005	Tunayama; Tomomi et al.

		apparatus, and magnetic memory			
US 6751074 B2	20040615	Magnetic memory having antiferromagnetically coupled recording layer	360/324.2	257/E21.665; 257/E27.005; 365/171; 365/173	Inomata; Koichiro et al.
US 6730949 B2	20040504	Magnetoresistance effect device	257/295	257/298; 257/301; 257/E43.004; 365/158; 365/171; 365/173	Kishi; Tatsuya et al.
US 6717845 B2	20040406	Magnetic memory	365/173	365/158; 365/171	Saito; Yoshiaki et al.
US 6710984 B1	20040323	Magnetoresistive effect device utilizing a magnetization-coupling layer which couples adjacent ferromagnetic layers perpendicularly	360/324.11		Yuasa; Hiromi et al.
US 6707711 B2	20040316	Magnetic memory with reduced write current	365/158	257/E21.665; 257/E27.005; 365/173	Saito; Yoshiaki et al.
US 6690553 B2	20040210	Magnetoresistance effect device, magnetic head therewith, magnetic recording/reproducing head, and magnetic storing apparatus	360/324.12	257/E21.665; 257/E27.005	Iwasaki; Hitoshi et al.
US 6636399 B2	20031021	Magnetoresistance effect device, magnetic head therewith, magnetic recording/reproducing head, and magnetic storing apparatus	360/324.12	257/E21.665; 257/E27.005	Iwasaki; Hitoshi et al.
US 6611405 B1	20030826	Magnetoresistive element and magnetic memory device	360/324.2	257/E21.665; 257/E27.005; 365/171; 365/173	Inomata; Koichiro et al.
US 6605836 B2	20030812	Magnetoresistance effect device,	257/295	257/E21.665; 257/E27.005;	Kishi; Tatsuya et al.

		magnetic memory apparatus, personal digital assistance, and magnetic reproducing head, and magnetic information		324/252; 365/158; 365/171; 365/173; 428/212	al.
US 6590803 B2	20030708	Magnetic memory device	365/158	365/171; 365/173	Saito; Yoshiaki et al.
US 6556473 B2	20030429	Magnetic memory with reduced write current	365/158	257/E21.665; 257/E27.005; 365/173	Saito; Yoshiaki et al.
US 6495275 B2	20021217	Multi-layered thin-film functional device and magnetoresistance effect element	360/324.11	360/324.12; 427/131; 427/548; 428/702; 428/816	Kamiguchi; Yuzo et al.
US 6483673 B1	20021119	Differential detection magnetoresistance head with laminated structure	360/324.11		Iwasaki; Hitoshi et al.
US 6395388 B1	20020528	Magnetoresistance effect element	428/332	257/E43.004; 257/E43.005; 324/252; 428/336; 428/810; 428/811; 428/900	Iwasaki; Hitoshi et al.
US 6369992 B1	20020409	Yoke-type head with magneto-resistance effect film recessed from medium facing surface and extending across magnetic gap	360/321	360/324.1	Yoda; Hiroaki et al.
US 6368706 B1	20020409	Magnetoresistance effect element	428/332	257/E43.004; 324/252; 428/336; 428/810; 428/811.1; 428/900	Iwasaki; Hitoshi et al.
US 6348274 B1	20020219	Magnetoresistive element and magnetic recording apparatus	428/811	360/313; 428/815; 428/900	Kamiguchi; Yuzo et al.
US 6338899 B1	20020115	Magnetoresistance effect element, magnetic head,	360/324.12	324/252; 338/32R; 360/324.11;	Fukuzawa; Hideaki et al.

		magnetic head assembly, magnetic storage system		428/336; 428/811; 428/811.2; 428/900	
US 6307708 B1	20011023	Exchange coupling film having a plurality of local magnetic regions, magnetic sensor having the exchange coupling film, and magnetic head having the same	360/126	360/321	Yoda; Hiroaki et al.
US 6303218 B1	20011016	Multi-layered thin-film functional device and magnetoresistance effect element	428/332	360/313; 428/336; 428/811.2; 428/811.5; 428/816; 428/900	Kamiguchi; Yuzo et al.
US 6285531 B1	20010904	Magnetic head with magneto-resistance effect element disposed on opposite side of magnetic core pair from recording coil	360/317	360/321	Ohsawa; Yuichi et al.
US 6256863 B1	20010710	Yoke type magnetoresistance head and manufacturing method of the same	29/603.08	148/108; 360/317	Saito; Kazuhiro et al.
US 6256171 B1	20010703	Thin film magnetic head having an improved heat dispersion and magnetic recording apparatus using the same	360/235.3	977/934	Yoda; Hiroaki et al.
US 6172858 B1	20010109	Thin film head	360/313	29/603.03	Yoda; Hiroaki et al.
US 6159593 A	20001212	Magnetoresistance effect element	428/811.2	257/E43.004; 324/252; 428/336; 428/900	Iwasaki; Hitoshi et al.
US 6157525	20001205	Magnetic head	360/324.12		Iwasaki;

A					Hitoshi et al.
US 6146776 A	20001114	Magneto-resistance effect head	428/811.3	324/252; 360/324.12; 428/900	Fukuzawa; Hideaki et al.
US 6118624 A	20000912	Magneto-resistance effect element having a magnetic biasing film	360/324.12	257/E43.004	Fukuzawa; Hideaki et al.
US 6118621 A	20000912	Magnetoresistance effect head having a pair of protrusions, steps or depressions between the detecting and nondetecting areas for improved off-track characteristics	360/327	360/322; 360/324.1	Ohsawa; Yuichi et al.
US 6111729 A	20000829	Magnetoresistance effect element	360/324.1		Kamiguchi; Yuzo et al.
US 6111722 A	20000829	Magnetoresistance effect element having improved biasing films, and magnetic head and magnetic recording device using the same	360/324.12	257/E43.004	Fukuzawa; Hideaki et al.
US 6088195 A	20000711	Magnetoresistance effect element	360/324.12	257/E43.004	Kamiguchi; Yuzo et al.
US 6069820 A	20000530	Spin dependent conduction device	365/171	257/E27.103; 257/E43.004; 365/173	Inomata; Koichiro et al.
US 6064552 A	20000516	Magnetoresistive head having magnetic yoke and giant magnetoresistive element such that a first electrode is formed on the giant magnetoresistive element which in turn is formed on the magnetic yoke which acts as a second electrode	360/322	360/321	Iwasaki; Hitoshi et al.
US 6052262	20000418	Magneto-resistance	360/324.12	257/E43.004	Kamiguchi;

A		effect element and magnetic head			Yuzo et al.
US 6046891 A	20000404	Thin film head	360/324.1		Yoda; Hiroaki et al.
US 6043515 A	20000328	Optical semiconductor device	257/103	257/81; 257/97; 257/99; 372/106; 372/45.01; 372/70; 372/75	Kamiguchi; Yuzo et al.
US 6038101 A	20000314	Magnetic head and method of manufacturing magnetic head	360/235.2		Yoda; Hiroaki et al.
US 5999378 A	19991207	Magnetoresistance effect head having a giant magnetoresistance effect film	360/324		Saito; Kazuhiro et al.
US 5991125 A	19991123	Magnetic head	360/324.12		Iwasaki; Hitoshi et al.
US 5962905 A	19991005	Magnetoresistive element	257/421	257/422; 257/423; 257/427; 257/E29.323; 257/E43.004; 257/E43.005	Kamiguchi; Yuzo et al.
US 5949622 A	19990907	Magnetoresistance effect element	360/324.12	257/E43.004	Kamiguchi; Yuzo et al.
US 5946167 A	19990831	Magnetoresistive sensor having lead and/or bias layer structure contributing to a narrow gap	360/322		Hara; Michiko et al.
US 5912790 A	19990615	Thin film magnetic recording-reproducing head having a high recording density and high fidelity	360/322	360/122; 360/317	Yoda; Hiroaki et al.
US 5905611 A	19990518	Thin film magnetic head responsive to spin-dependent	360/324.1		Yoda; Hiroaki et al.

		scattering			
US 5896251 A	19990420	Magnetoresistance effect head with conductor film pair and magnetic field proving film pair disposed between substrate and magnetoresistance effect film	360/324		Ohsawa; Yuichi et al.
US 5828525 A	19981027	Differential detection magnetoresistance head	360/314		Iwasaki; Hitoshi et al.
US 5818684 A	19981006	Shield type magnetoresistive head arranged for weakening of a galvano-current magnetic field	360/319		Iwasaki; Hitoshi et al.
US 5796560 A	19980818	Magnetoresistive head	360/324		Saito; Kazuhiro et al.
US 5780176 A	19980714	Magnetoresistance effect element	428/811.2	257/E43.004; 257/E43.005; 324/252; 360/324.11; 360/327.32; 428/610; 428/670; 428/675; 428/676; 428/678; 428/900	Iwasaki; Hitoshi et al.
US 5777542 A	19980707	Magnetoresistance effect device and manufacturing method thereof	338/32R	257/E43.004; 29/603.08; 360/320	Ohsawa; Yuichi et al.
US 5773156 A	19980630	Magnetoresistance effect element	428/611	257/E43.005; 338/32R; 360/324; 428/546; 428/620; 428/641	Inomata; Koichiro et al.
US 5768066 A	19980616	Magnetoresistive head having an antiferromagnetic	360/314		Akiyama; Junichi et al.

		layer interposed between first and second magnetoresistive elements			
US 5756191 A	19980526	Exchange coupling film and magnetoresistance effect element	428/209	257/E43.005; 324/252; 360/327.32; 428/688	Hashimoto; Susumu et al.
US 5738946 A	19980414	Magnetoresistance effect element	428/811.2	257/E43.004; 257/E43.005; 324/252; 360/324.1; 428/615; 428/652; 428/668; 428/670; 428/671; 428/900; 428/928	Iwasaki; Hitoshi et al.
US 5725963 A	19980310	Magnetoresistance effect element	428/811.2	257/E43.004; 257/E43.005; 324/252; 360/324.12; 428/622; 428/627; 428/629; 428/632; 428/639; 428/641; 428/660; 428/667; 428/670; 428/678; 428/900; 428/928	Iwasaki; Hitoshi et al.
US 5702832 A	19971230	Magnetoresistance effect element	428/611	257/E43.004; 257/E43.005; 324/252; 360/324.1; 428/622; 428/627; 428/629; 428/632; 428/639; 428/641;	Iwasaki; Hitoshi et al.

				428/660; 428/667; 428/670; 428/678; 428/811.2; 428/900; 428/928	
US 5700588 A	19971223	Magnetoresistance effect element	428/611	257/E43.005; 428/635; 428/670; 428/673; 428/675; 428/928	Saito; Yoshiaki et al.
US 5698335 A	19971216	Magnetoresistance effect element having bias films	428/611	257/E43.004; 257/E43.005; 324/252; 360/324.1; 428/622; 428/627; 428/629; 428/632; 428/639; 428/641; 428/660; 428/667; 428/670; 428/678; 428/811.2; 428/900	Iwasaki; Hitoshi et al.
US 5688605 A	19971118	Magnetoresistance effect element	428/811.2	257/E43.004; 257/E43.005; 324/252; 360/324.1; 428/622; 428/668; 428/671; 428/672; 428/673; 428/674; 428/675; 428/928	Iwasaki; Hitoshi et al.
US 5616370 A	19970401	Artificial multilayer and method of manufacturing the same	427/547	204/192.2; 257/E43.005; 427/128; 427/130; 427/131;	Okuno; Shiho et al.

				427/598	
US 5607781 A	19970304	Oxide film with preferred crystal orientation, method of manufacturing the same, and magneto-optical recording medium	428/822.1	204/192.1; 204/192.11; 204/192.14; 204/192.15; 204/192.2; 204/192.26; 252/62.51C; 252/62.51R; 252/62.56; 369/13.35; 427/128; 427/595; 427/599; 428/702; 428/900	Okuno; Shiho et al.
US 5587026 A	19961224	Ferromagnetic film	148/313	420/435	Iwasaki; Hitoshi et al.
US 5585199 A	19961217	Magnetoresistance effect head	428/621	360/324; 428/611; 428/928	Kamiguchi; Yuzo et al.
US 5585196 A	19961217	Magnetoresistance effect element	428/811.3	257/E43.005; 360/126; 360/324; 428/336; 428/402; 428/558; 428/561; 428/611; 428/615; 428/671; 428/675; 428/900	Inomata; Koichiro et al.
US 5578385 A	19961126	Magnetoresistance effect element	428/611	257/E43.005; 428/635; 428/670; 428/673; 428/675; 428/928	Saito; Yoshiaki et al.
US 5576915 A	19961119	Magnetoresistive head with antiferromagnetic sublayers interposed between first and second spin-valve	360/314		Akiyama; Junichi et al.

		units to exchange bias inner magnetic films thereof			
US 5552949 A	19960903	Magnetoresistance effect element with improved antiferromagnetic layer	360/327.32	257/E43.004; 324/252; 338/32R	Hashimoto; Susumu et al.
US 5549978 A	19960827	Magnetoresistance effect element	428/811.2	257/E43.004; 257/E43.005; 324/252; 360/324.1; 428/611; 428/622; 428/627; 428/629; 428/632; 428/639; 428/641; 428/660; 428/667; 428/670; 428/678; 428/900	Iwasaki; Hitoshi et al.
US 5534355 A	19960709	Artificial multilayer and method of manufacturing the same	428/811.3	257/E43.005; 324/252; 360/126; 360/324; 427/131; 427/547; 427/598; 428/212; 428/336; 428/635; 428/662; 428/667; 428/668; 428/672; 428/674; 428/680; 428/681; 428/900; 428/928	Okuno; Shiho et al.
US 5523172 A	19960604	Magnetoresistance effect element	428/611	257/E43.005; 428/635; 428/670;	Saito; Yoshiaki et al.

				428/673; 428/675; 428/928	
US 5500633 A	19960319	Magnetoresistance effect element	338/32R	257/E43.005; 324/252	Saito; Yoshiaki et al.
US 5493465 A	19960220	Magnetoresistance effect element and magnetic recording apparatus	360/324.1	257/E43.004; 324/207.21; 338/32R	Kamiguchi; Yuzo et al.
US 5484491 A	19960116	Ferromagnetic film	148/313	420/435	Iwasaki; Hitoshi et al.
US 5461527 A	19951024	Magneto-resistive head	360/327.32		Akiyama; Junichi et al.
US 5416353 A	19950516	Netoresistance effect element	257/421	257/425; 257/427; 257/536; 257/E43.004	Kamiguchi; Yuzo et al.
US 5365212 A	19941115	Magnetoresistance effect element	338/32R	257/E43.005; 324/252	Saito; Yoshiaki et al.
US 5329413 A	19940712	Magnetoresistance sensor magnetically coupled with high- coercive force film at two end regions	360/327.32		Kondoh; Reiko et al.
US 5304975 A	19940419	Magnetoresistance effect element and magnetoresistance effect sensor	338/32R	257/E43.005; 324/252; 360/324	Saito; Yoshiaki et al.